查询CEN-U45供应商

Data Sheet

Central™
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Manufacturers of World Class Discrete Semiconductors

CEN-U45

NPN SILICON DARLINGTON TRANSISTOR

JEDEC TO-202 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CEN-U45 type is a NPN Silicon Monolithic Darlington Transistor designed for applications requiring high gain and high power dissipation.

MAXIMUM RATINGS (T_A=25°C)

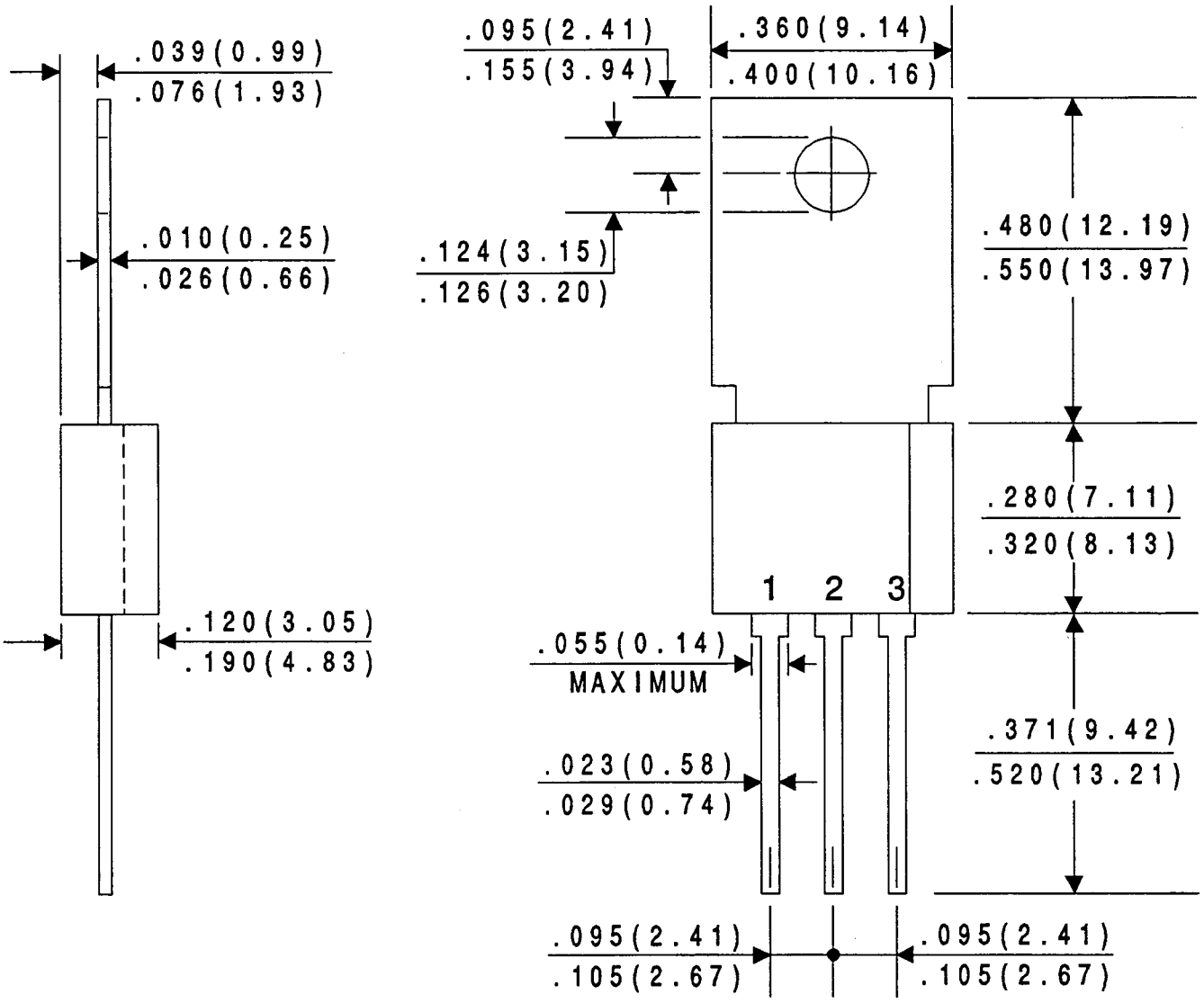
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CES}	40	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	12	V
Collector Current	I_C	2.0	A
Power Dissipation	P_D	2.0	W
Power Dissipation (T_C=25°C)	P_D	10	W
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	62.5	°C/W
Thermal Resistance	Θ_{JC}	12.5	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	V_{CB}=30V		100	nA
I_{EBO}	V_{EB}=10V		100	nA
BV_{CBO}	I_C=100μA	50		V
BV_{CES}	I_C=100μA	40		V
BV_{EBO}	I_E=10μA	12		V
$V_{CE(SAT)}$	I_C=1.0A, I_B=200mA		1.0	V
$V_{BE(SAT)}$	I_C=1.0A, I_B=200mA		2.0	V
$V_{BE(ON)}$	V_{CE}=5.0V, I_C=1.0A		2.0	V
h_{FE}	V_{CE}=5.0V, I_C=200mA	25K	150K	
h_{FE}	V_{CE}=5.0V, I_C=500mA	15K		
h_{FE}	V_{CE}=5.0V, I_C=1.0A	4.0K		
f_T	V_{CE}=5.0V, I_C=200mA, f=100MHz	100		MHz
C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz		8.0	pF

(SEE REVERSE SIDE)

JEDEC TO-202 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

LEAD CODE:

1) EMITTER
2) BASE
3) COLLECTOR

Central Semiconductor Corp.